MT2302

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

PRODUCT SUMMARY				
V _{DSS}	Id	$RDS(ON)$ $(m \Omega)$ Typ		
20V	3.6A	36@ VGS=4.5V		
		45@ VGS=2.5V		

Features

- Super high dense cell design for low RDS(ON)
- · Rugged and reliable
- Simple drive requirement
- · SOT-23 package

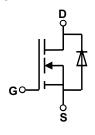
Applications

- · Notebook Computer
- · Portable Battery Pack

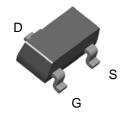


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Simplified Schematic



MARKING DIAGRAM & PIN ASSIGNMENT



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	20	V
Gate-Source Voltage	Vgs	±12	V
Drain Current-Continuous ^a @Tj=125°C	ID	3.6	A
- Pulse d^b	Ідм	12	A
Drain-source Diode Forward Current ^a	Is	1.25	A
Maximum Power Dissipation ^a	PD	1.25	W
Operating Junction and Storage Temperature Range	T _J ,Tstg	-55 to 150	$^{\circ}$ C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to Ambient ^a	Rth JA	100	°C/W

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Uni	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BVDSS	V _{GS} =0V,I _D =250μA	20			V	
Zero Gate Voltage Drain Current	IDSS	V _{DS} =16V,V _{GS} =0V			1	μД	
Gate-Body Leakage	Igss	$V_{GS}=\pm 8V, V_{DS}=0V$			±100	nA	
ON CHARACTERITICS							
Gate Threshold Voltage	Vgs(th)	$V_{DS}=V_{GS},I_{D}=-250\mu A$	0.5	0.8	1.5	V	
D : 0 0 0 1 D : 1	D	V _G s=4.5V,I _D =2.8A		36	41	0	
Drain-Source On-State Resistance	Rds(on)	Vgs=2.5V,Id=2.0A		45	51	mΩ	
Forward Transconductance	gFS	V _{GS} =5V,I _D =5A		5		S	
DYNAMIC CHARACTERISTICS					1		
Input Capacitance	Ciss			586		pF	
Output Capacitance	Coss	$V_{DS}=10V,V_{GS}=0V$ f=1.0MHz		101		pF	
Reverse Transfer Capacitance	Crss	I I.OIVIIIZ		59		pF	
SWITCHING CHARACTERISISTICS					•		
Turn-On Delay Time	tD(ON)	V _{DD} =10V		6.5		ns	
Rise Time	tr	I _D =3.6A,		32.1		ns	
Turn-Off Delay Time	td(off)	V _{GEN} =4.5V R _L =10ohm		58.4		ns	
Fall Time	tf	RGEN=10ohm		48		ns	
Total Gate Charge	Qg			6		nC	
Gate-Source Charge	Qgs	V _{DS} =10V,I _D =1A V _{GS} =4.5V		1.35		nC	
Gate-Drain Charge	Qgd	v GS=4.5 v		1.5		nC	

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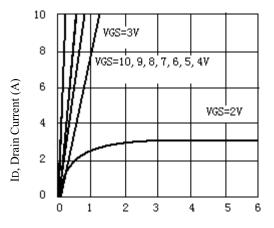
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ELECTRICAL CHARACTERICS (TA=25°C unless otherwise noted)

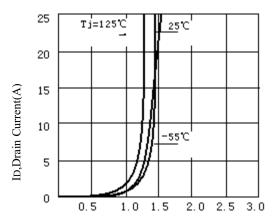
Parameter	Symbol Condition		Min	Тур	Max	Unit	
DRAIN-SOURCE DIODE CHARACTERISTICS							
Diode Forward Voltage	VSD VGS=0V,Is=1.25A			0.84	1.2	V	

Notes

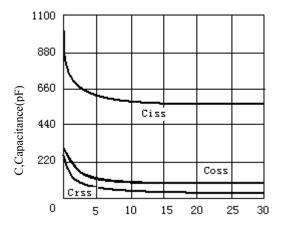
- a. Surface Mounted on FR4 Board, t≤10sec
- b. Pulse Test: Pulse Width ≤ 300Us, Duty Cycle ≤ 2%
- c. Guaranteed by design, not subject to production testing.



VDS, Drain-to-Source Voltage (V) Figure 1. Output Characteristics



VGS, Gate-to-source Voltage (V) Figure 2. Transfer Characteristics



VGS, Drain-to Source Voltage Figure3. Capacitance

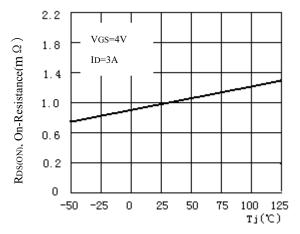
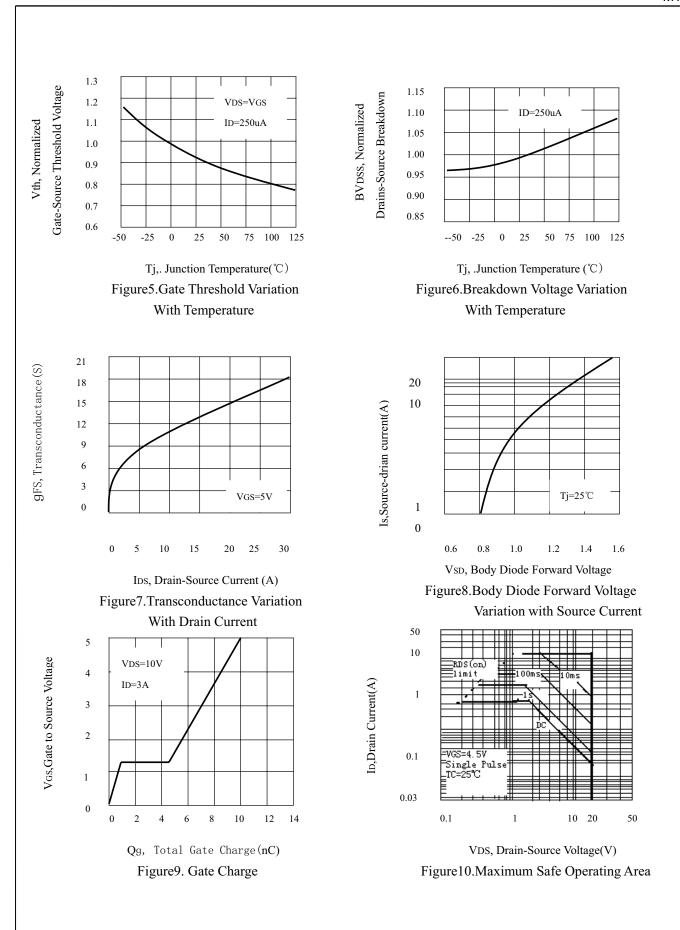


Figure 4. On-Resistance Variation with $\label{eq:condition} Temperature$

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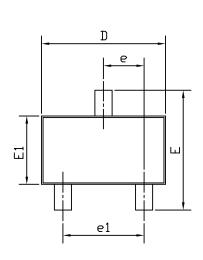
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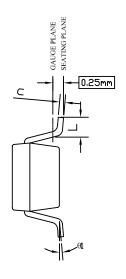


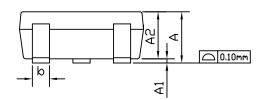
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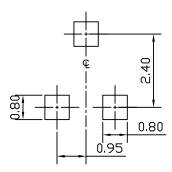
SOT23 PACKAGE OUTLINE







RECOMMENDED LAND PATTERN



UNIT: mm

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
STWBOLS	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85		1.25	0.033		0.049
A1	0.00		0.13	0.000		0.005
A2	0.70	1.00	1.15	0.028	0.039	0.045
b	0.30	0.40	0.50	0.012	0.016	0.020
С	0.08	0.13	0.20	0.003	0.005	0.008
D	2.80	2.90	3.10	0.110	0.114	0.122
Е	2.60	2.80	3.00	0.102	0.110	0.118
E1	1.40	1.60	1.80	0.055	0.063	0.071
e	0.95 BSC				0.037 BSC	
e1	1.90 BSC				0.075 BSC	
L	0.30		0.60	0.012		0.024
θ1	0°	5°	8°	0°	5°	8°

NOTE

- 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH OR GATE BURRS. MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 5 MILS EACH.
- 2. TOLERANCE ± 0.100 mm (4 mil) UNLESS OTHERWISE SPECIFIED.
- 3. DIMENSION L IS MEASURED IN GAUGE PLANE.
- 4. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.
- 5. ALL DIMENSIONS ARE IN MILLIMETERS.

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